

### **REMARKS**

The present amendment is in response to the Office Action received on June 3, 2005, in which Claims 13-20 were rejected. Applicant has thoroughly reviewed the outstanding Office Action including the Examiner's remarks and the reference cited therein. The following remarks are believed to be fully responsive to the Office Action and render all claims at issue patentably distinguishable over the cited references.

Reconsideration and withdrawal of the rejections set forth in the Office Action dated June 03, 2005 are respectfully requested.

#### **Claim Rejections - 35 U.S.C. § 112**

Applicant has amended Claim 18 so that the vagueness is eliminated. Therefore, the rejection of Claim 18 is overcome.

Referring to paragraph [0029] of the present application, which describes that "activity of preferred material of the resist region 20 is less than the gate line 12, because the gate line 12 will be corroded or oxidized after the resist region 20 is completely eroded or oxidized when both the passivation layer 22 and the gate insulating layer 14 are crack. The less activity of the resist region 20 is the longer duration of resist region 20 is eroded or oxidized, and possibility of gate line 12 eroding or oxidizing can be decreased." According to the the "American Heritage® Dictionary of the English Language," the word "activity" stands for "the ability to take part in a chemical reaction." Hence the scope of the amended Claim 18 is substantially the same as the original Claim 18, except the way of expression is changed to make Claim 18 clearer.

#### **Claim Rejections - 35 U.S.C. § 103**

The present invention provides a resist layer to protect the gate insulating layer and passivation layer from breaking. As set forth in Claim 13, such resist layer is placed *right beneath* the scribing line as well as covering the gate terminal and lead of the gate

electrode line. With the resist layer, the strength of the passivation layer and the gate insulating layer against the scribing strain of the second substrate is increased.

Applicant emphasizes that the resist region covers the gate terminal and the lead and is located at a scribing line on the margin of a second substrate with color filter thereon, as mentioned in the amended claim 13. The prior art fails to disclose such a feature. It should be noted that the precise position of the resist region is significant to the claimed invention.

However, according to West, the scribing step thereof would separate the whole device into a plurality of parts, and the "metal wall" and "rivets" are deposited respectively within each part to maintain the structure of overlaying layers. The "metal wall" and "rivets" do not bear the strain of the scribing procedure directly. In the present invention, the resist region is formed to withstand the scribing strain to prevent any other layers being damaged, but not to maintain the structure of overlaying layers. As matter of fact, West disclosed a sealing structure for a chip instead of a method for protecting a gate terminal for a liquid crystal panel. Referring to col. 7, line 65 to col. 8, line 8 of West, the seal structure, between the chip data edge and the dicing line, are composite discontinuous barrier walls comprising metal columns 150 and 151. These rivets 150 and 151 are arranged in an alternating pattern in order to provide the composite structure mechanical strength and prevent delamination. The elements 150, 151 are located between the chip data edge and the dicing line. West has no motivation and is unable to disclose the claimed invention. The ordinary person cannot achieve the claimed invention under his teaching.

Note that the scribing step of the present invention is performed after the second substrate and the first substrate are assembled. The second substrate is close to the passivation layer and the gate insulating layer, thus, the scribing of the second substrate would be very likely to damage these two layers. In order to achieve the effect of protecting the passivation layer and the gate insulating layer from breaking, the resist

region must be placed right beneath the scribing line, instead around the scribing line. Consequentially, the effect and result of the claimed invention is unexpected to the prior art, and the invention defined in Claim 13 is unobvious and patentable.

Where the disclosure of West is applied to the admitted prior art, the "metal wall" or "rivets" would be place in the second substrate because in the present invention only the second substrate is diced. The addition of "metal wall" or "rivets" in the second substrate is unnecessary. Therefore, the motivation to combine West and the admitted prior art does not exist. The invention defined in Claim 13 is unobvious and patentable.

Since Claims 14-17, 19 and 20 depend on Claim 13, they should be patentable under the patentability of Claim 13.

In view of the foregoing, Claims 13-20 pending in the application comply with the requirements of patentability define over the applied art. A Notice of Allowance is, therefore, respectfully requested.

Applicant believes no fee is due with this response. However, if a fee is due, please charge our Deposit Account No. 50-0665, under Order No. 386998033US from which the undersigned is authorized to draw.

Dated:

8/29/01

Respectfully submitted,

By 

Chun M. Ng

Registration No.: 36,878

PERKINS COIE LLP

P.O. Box 1247

Seattle, Washington 98111-1247

(206) 359-8000

(206) 359-7198 (Fax)

Attorney for Applicant